# V00027

Die; 2222; 850; M; 3B; Y12X45; 2W; 0.87X0.87

### **Features:**

- Chip Technology: GaAs VCSEL
- Laser Wavelength: 850 nm
- Optical Power Class: 2 W pulsed
- Radiation Profile: Multi-Mode
- ESD: 2 kV acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)

## **Ordering Information**

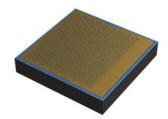
Description	Operating Mode:	Ordering Code
	T <sub>a</sub> = 25°C; I <sub>F</sub> = 2.3 A;	
	t <sub>p</sub> = 100 μs; DC = 1%	
Die; 2222; 850; M; 3B; Y12X45;	2 W	V00027
2W; 0.87X0.87		



ixar

**Opto Semiconductors** 

COMPLIES WITH IEC 60825-1, 3<sup>rd</sup> EDITION MAY 2014. COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER NOTICE NO.50 DATED 27 MAY 2001.



## **Maximum Ratings**

 $T_a = 25^{\circ}C$ 

Parameter	Symbol		Values
Operation/Solder temperature	Ts	min.	-40°C
t <sub>p</sub> = 100 μs; DC = 1%		max.	100°C
Storage temperature	T <sub>stg</sub>	min.	-40°C
		max.	100°C
Forward current	lf	max.	7 A
Pulsed operation; $T_p$ = 100 µs; DC = 1%; $T_S$ = 25°C			
Forward current	lf	max.	4.5 A
Direct current operation; DC = 100%; Ts = $25^{\circ}$ C			
Reverse Voltage	Not designed for reverse operation		
ESD withstand voltage	Vesd	max.	2 kV
acc. to ANSI/ESDA/JEDEC JS-001 (HBM, Class 2)			

Note: Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.



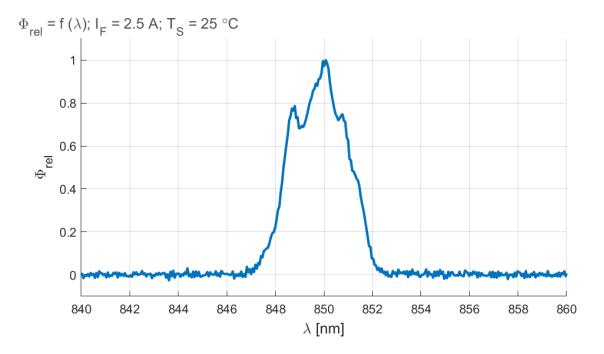
## **Characteristics**

 $T_a = 25^{\circ}C, \ I_F = 2.3 \ A; \ t_p = 100 \ \mu s; \ DC = 1\%$ 

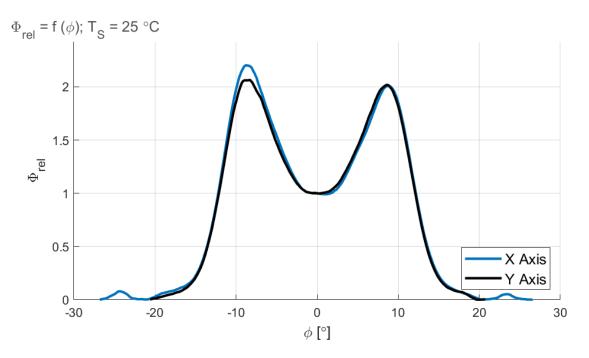
Parameter	Symbol		Values
Forward voltage	VF	typ.	2.2 V
Output power	Φ	typ.	2 W
Threshold current	l <sub>th</sub>	typ.	0.5 A
Slope efficiency	SE	typ.	1 W / A
Power conversion efficiency	η	typ.	41%
Peak wavelength	$\lambda_{peak}$	min.	840 nm
		typ.	850 nm
		max.	860 nm
Spectral bandwidth at FWHM (50% of $\Phi_{max}$ )	λfwhm	typ.	2 nm
Temperature coefficient of wavelength	TCλ	typ.	0.06 nm / K
Field of view at FWHM (50% of $\Phi_{max}$ )	<b>ф</b> х	typ.	20°
	<b>¢</b> Y	typ.	20°



### **Relative Spectral Emission** <sup>1)</sup>

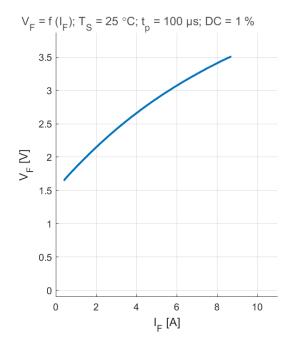


#### Radiation Characteristics <sup>1)</sup>

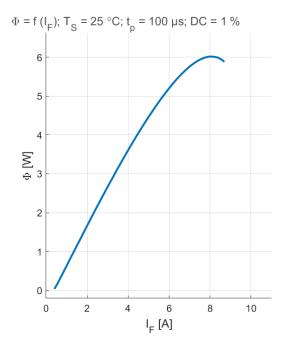




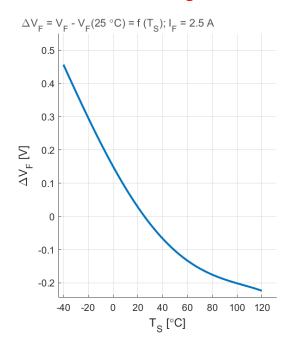
### Forward Voltage <sup>1) 2)</sup>



## Optical Output Power <sup>1) 2)</sup>

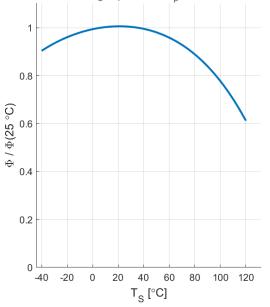


#### **Relative Forward Voltage** <sup>1)</sup>

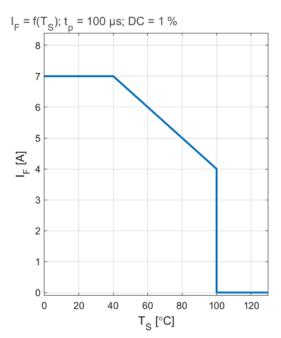


#### **Relative Radiant Power**<sup>1)</sup>

 $\Phi$  /  $\Phi(25~^\circ\text{C})$  = f (T\_s); I\_F = 2.5 A; t\_p = 100 \ \mu\text{s; DC} = 1 %

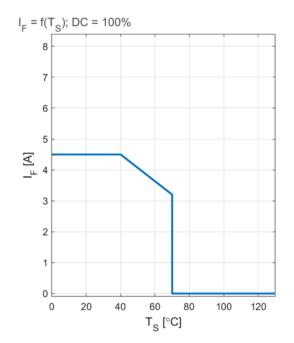






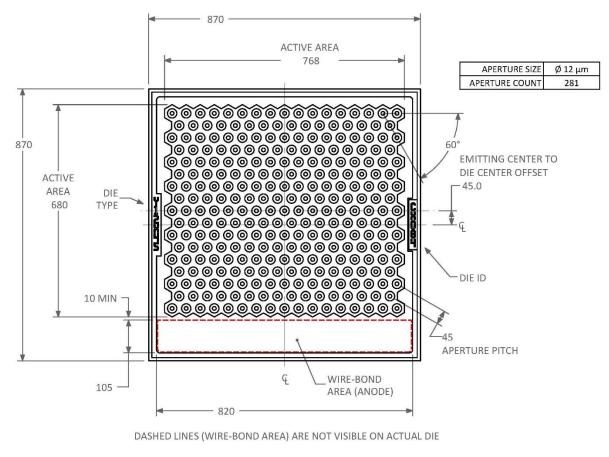
#### Max Permissible Pulse Current

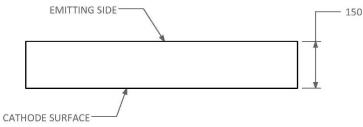
#### **Max Permissible Current**





#### **Dimension Drawings**<sup>3)</sup>







## **Product Label**

VIXAR Vertical Cavity Surface Emitting Laser (VCSEL) Product		
Model:		
Manufacturer: VIXAR 2355 Polaris AVE N. SUITE 100 Plymouth, MN 55447 USA		
Manufactured: Bare Die by VIXAR, Fabricated or Packaged by: City:, Country:		
Wafer #: Date Code: Manufacturer Lot No.: Quantity:		
Complies with FDA/CDRH 21 CFR 1040.10 and 1040.11 except for deviations pursuant to Laser Notice No. 50, dated June 24, 2007.		
CDRH Accession No.: 1210159-000	Product Code: RDW	



## Notes

Depending on the mode of operation, these devices emit highly concentrated visible and non-visible light which can be hazardous to the human eye. Products which incorporate these devices must follow the safety precautions given in IEC 60825-1.

Subcomponents of this device contain, in addition to other substances, metal filled materials including silver. Metal filled materials can be affected by environments that contain traces of aggressive substances. Therefore, we recommend that customers minimize device exposure to aggressive substances during storage, production, and use. Devices that showed visible discoloration when tested using the described tests above did show no performance deviations within failure limits during the stated test duration. Respective failure limits are described in the IEC60810.

For further application related information please visit vixarinc.com/vcsel-technology/application-notes



## Glossary

- Typical Values: Due to the special conditions of the manufacturing processes of semiconductor devices, the typical data or calculated correlations of technical parameters can only reflect statistical figures. These do not necessarily correspond to the actual parameters of each single product, which could differ from the typical data and calculated correlations or the typical characteristic line. If requested, e.g. because of technical improvements, these typ. data will be changed without any further notice.
- <sup>2)</sup> **Testing temperature:**  $T_a = 25^{\circ}C$
- <sup>3)</sup> **Tolerance of Measure:** Unless otherwise noted in drawing, tolerances are specified with ±0.1 and dimensions are specified in mm.



## **Revision History**

Version	Date	Change
0.0	November 24, 2020	Initiation of preliminary datasheet
1.0	January 21, 2021	Release of datasheet



COMPLIES WITH IEC 60825-1, 3<sup>rd</sup> EDITION MAY 2014. COMPLIES WITH 21 CFR 1040.10 AND 1040-10.11 EXCEPT FOR DEVIATIONS PURSUANT TO LASER NOTICE NO.50 DATED 27 MAY 2001.

